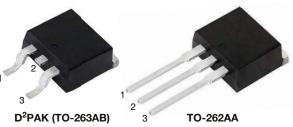
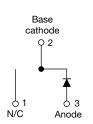
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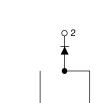
VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 15 A







01

N/C

VS-HFA15 TB60S-M3

VS-HFA15 TB60-1-M3

3

Anode

PRIMARY CHARACTERISTICS								
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	1.2 V							
t _{rr} (typ.)	23 ns							
T _J max.	150 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Single							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA15TB60S, VS-HFA15TB60-1 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60S, VS-HFA15TB60-1 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60S, VS-HFA15TB60-1 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		600	V				
Maximum continuous forward current	I _F	T _C = 100 °C	15					
Single pulse forward current	I _{FSM}		150	А				
Maximum repetitive forward current	I _{FRM}		60					
Maximum neuror dissinction	D	T _C = 25 °C	74	W				
Maximum power dissipation	PD	T _C = 100 °C	29	vv				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				

RoHS COMPLIANT HALOGEN

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Document Number: 96313

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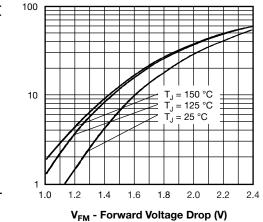
ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-		
		I _F = 15 A	- 1.3 See fig. 1 - 1.5 - 1.2	1.7	V			
Maximum forward voltage	V _{FM}	I _F = 30 A		-	1.5	2.0		
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6		
Maximum reverse		$V_{R} = V_{R}$ rated	Coofin 0	-	1.0	10		
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	400	1000	μA	
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	25	50	pF	
Series inductance	LS	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH	

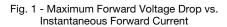
DYNAMIC RECOVERY	CHARAC	TERISTICS ($T_J = 25$	°C unless otherwise	e specifie	d)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	A/μs, V _R = 30 V	-	23	-	
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C		-	50	60	ns
	t _{rr2}	T _J = 125 °C		-	105	120	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	6.0	А
See fig. 6	I _{RRM2}	T _J = 125 °C	I _F = 15 A	-	6.5	10	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	84	180	nC
See fig. 7	Q _{rr2}	T _J = 125 °C	v _R = 200 v	-	241	600	110
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A/µs
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	

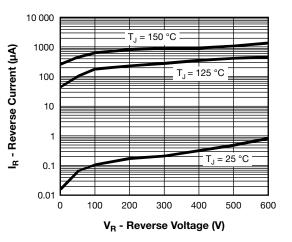
THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7					
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	80	K/W				
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Marking davias		Case style D ² PAK (TO-263AB)		HFA15	TB60S					
Marking device		Case style TO-262AA		HFA15	TB60-1					

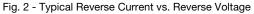


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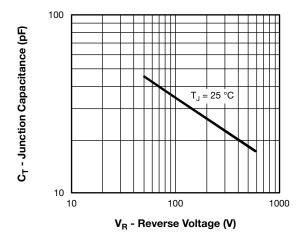
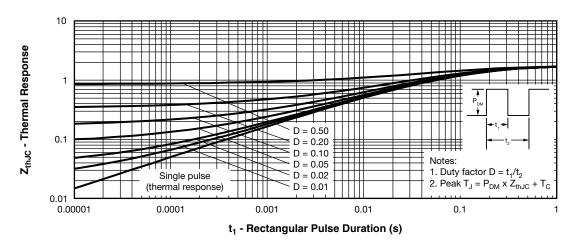


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





I_F - Instantaneous Forward Current (A)



I_{rr} (A)

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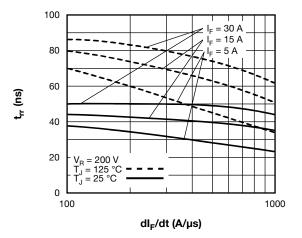


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

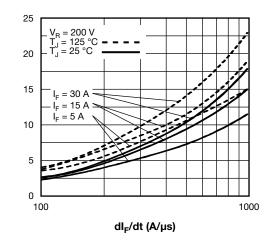


Fig. 6 - Typical Recovery Current vs. dl_F/dt

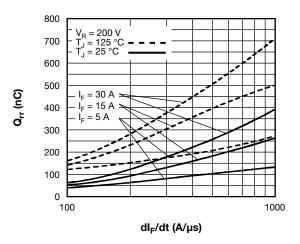


Fig. 7 - Typical Stored Charge vs. dl_F/dt

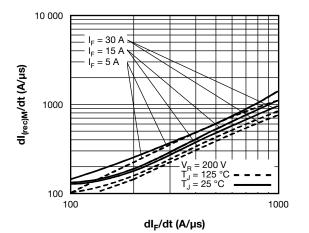


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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4

Document Number: 96313

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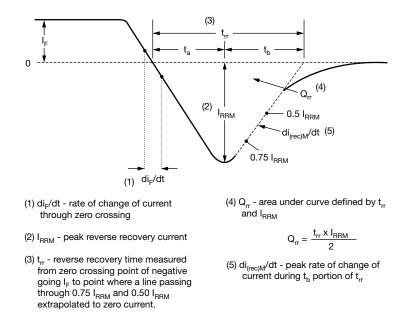


Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	15	тв	60	S	L	-M3	
		(2)	(3)	4	(5)	6	(7)	(8)	(9)	
	1 ·	· Visl	nay Sen	niconduo	ctors pro	oduct		0		
	2	· HE	xFRED [@]	[®] family						
	3 ·	Ele	ctron irra	adiated						
	4	· Cur	rent rati	ng (15 =	= 15 A)					
	5		kage: = TO-22	20						
	6	· Volt	tage rati	ng (60 =	= 600 V))				
	7	• S	= D ² PA	K (TO-2	63AB)					
	<u> </u>	• -1	= TO-2	62AA						
	8 -	• N	one = tu	ibe (50 j	oieces)					
		۰L	= tape a	and reel	(left orie	ented, fo	or D ² PA	К (ТО-2	263AB)	package)
		• R	= tape a	and reel	(right o	riented,	for D ² F	PAK (TC)-263AB) package
	9 -	-M3	s = halog	gen-free	, RoHS-	-complia	ant, and	termina	ations le	ad (Pb)-fre

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-HFA15TB60S-M3	50	Antistatic plastic tube					
VS-HFA15TB60SL-M3	800	13" diameter reel					
VS-HFA15TB60SR-M3	800	13" diameter reel					
VS-HFA15TB60-1-M3	50	Antistatic plastic tube					

	LINKS TO RELATED DOCUMENTS								
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164							
	TO-262AA	www.vishay.com/doc?96165							
Part and the lafe method	D ² PAK (TO-263AB)	www.vishay.com/doc?95444							
Part marking information	TO-262AA	www.vishay.com/doc?95443							
Packaging information		www.vishay.com/doc?96424							
SPICE model		www.vishay.com/doc?95357							

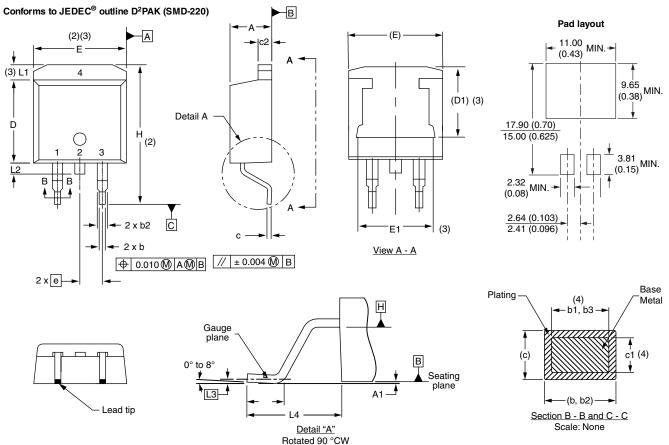
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D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIM	MILLIMETERS		HES	NOTES	
STMBOL	MIN.	MIN. MAX. MIN.		MAX.	NOTES	
A	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC) BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

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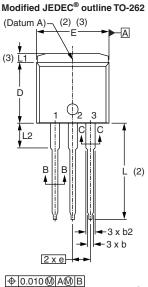
Outline Dimensions

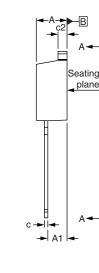


Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches



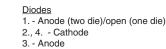


D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None

E

010	(M) A	.@/E	3		
_				_	
	math	math.	mark		





Lead assignments

SYMBOL	MILLIN	METERS	INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second flash include mold flash. the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

1

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